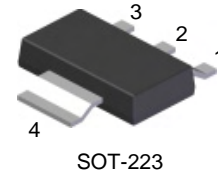


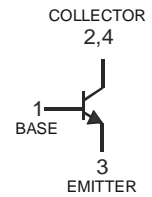
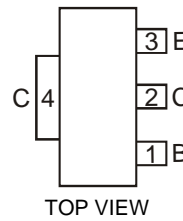
Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DZT591C)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Continuous Current (Note 3)	I_C	1	A
Peak Collector Current	I_{CM}	2	A
Base Current	I_B	200	mA
Power Dissipation (Note 3)	P_d	1	W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Cutoff Current	I_{CBO}	—	—	100	nA	$V_{CB} = 60\text{V}$
Emitter-Base Cutoff Current	I_{EBO}	—	—	100	nA	$V_{EB} = 4\text{V}$
Collector-Emitter Cutoff Current	I_{CES}	—	—	100	nA	$V_{CES} = 60\text{V}$
Collector-Base Breakdown Voltage	$V_{(BR)CB0}$	80	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	60	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 100\mu\text{A}$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	0.25	V	$I_C = 500\text{mA}, I_B = 50\text{mA}$
		—	—	0.5	V	$I_C = 1\text{A}, I_B = 100\text{mA}$
DC Current Gain	h_{FE}	100	—	—	—	$V_{CE} = 5\text{V}, I_C = 1\text{mA}$
		100	—	300	—	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$
		80	—	—	—	$V_{CE} = 5\text{V}, I_C = 1\text{A}$
		30	—	—	—	$V_{CE} = 5\text{V}, I_C = 2\text{A}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	1.1	V	$I_C = 1\text{A}, I_B = 100\text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	—	—	1	V	$I_C = 1\text{A}, V_{CE} = 5\text{V}$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f_T	150	—	—	MHz	$V_{CE} = 10\text{V}, I_C = 50\text{mA}, f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	10	pF	$V_{CB} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 4. Measured under pulsed conditions. Pulse width = 300ms duty cycle $\leq 2\%$

Typical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

NEW PRODUCT

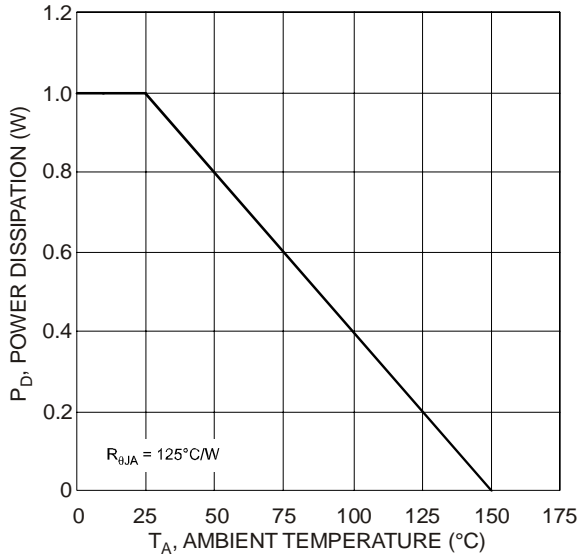


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

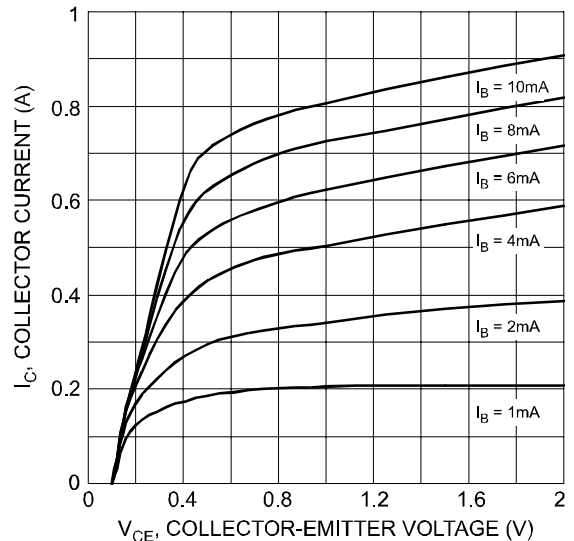


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

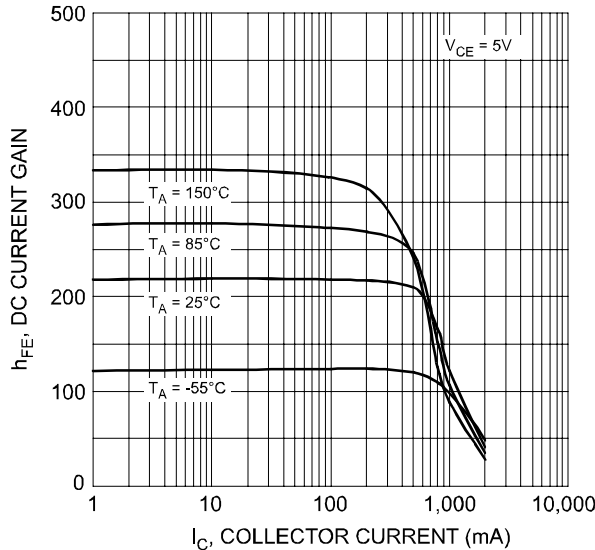


Fig. 3 Typical DC Current Gain vs. Collector Current

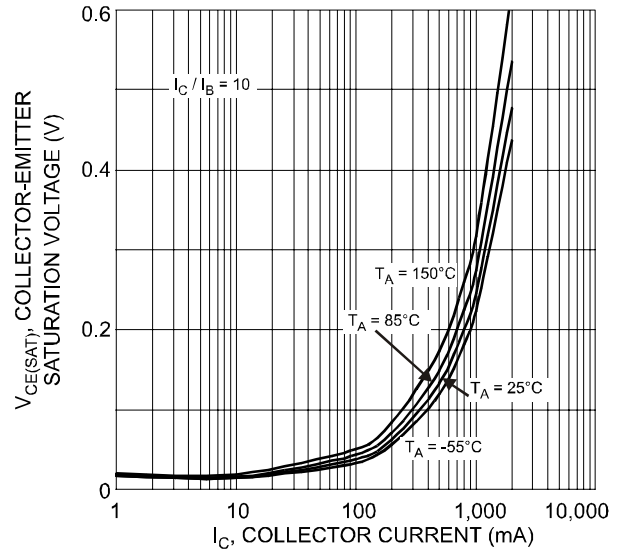


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

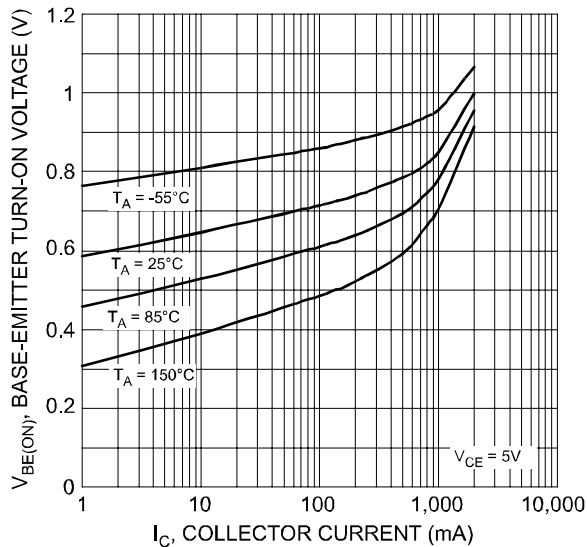


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

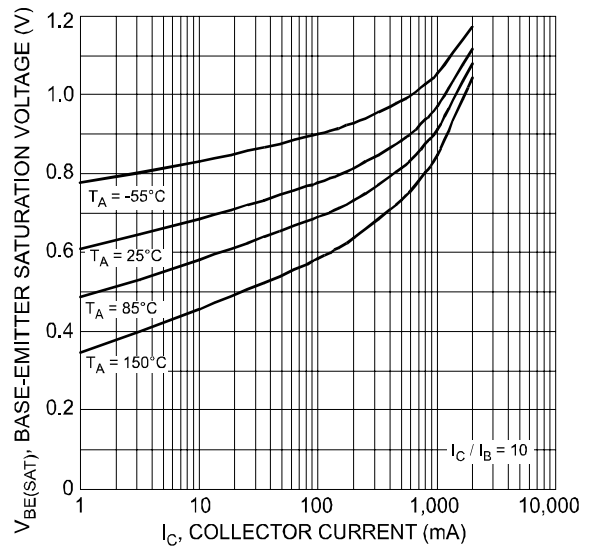


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

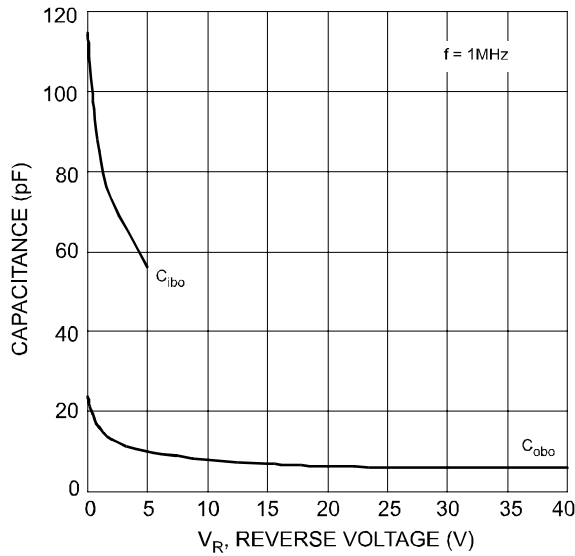


Fig. 7 Typical Capacitance Characteristics

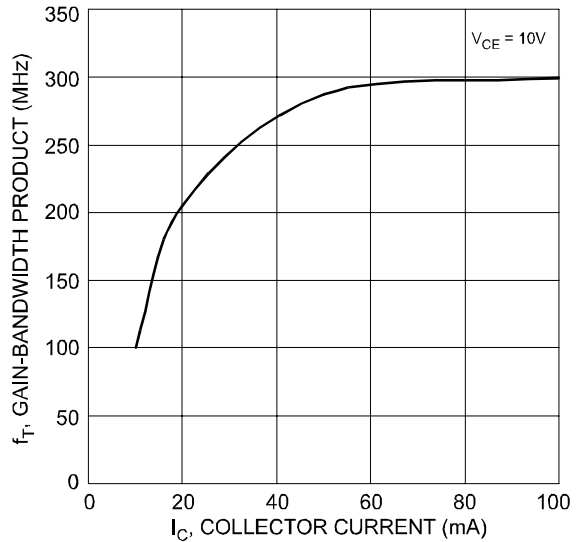


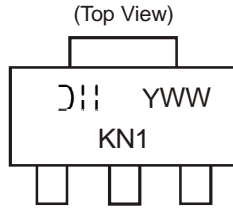
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DZT491-13	SOT-223	2500/Tape & Reel

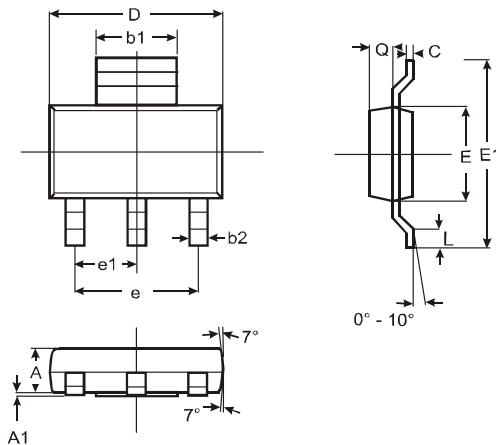
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



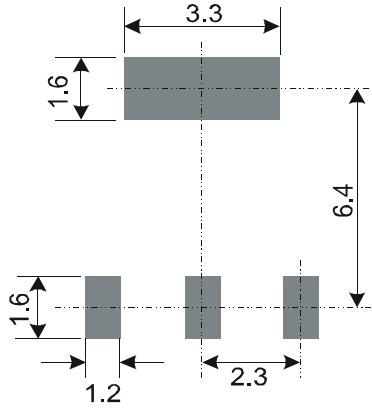
DII = Manufacturer's code marking
KN1 = Product type marking code
YWW = Date code marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout: (Based on IPC-SM-782)



(Unit: mm)

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